Substitute for form 1449A/PTO **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** *(Use as many sheets as necessary)*	Complete if Known	
	Application Number	~~Unknown~~ 10/790,510
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	First Named Inventor	Forbes, Leonard
	Group Art Unit	~~Unknown~~ 2823
	Examiner Name	~~Unknown~~ W. DAVID COLEMAN
Sheet 1 of 3	Attorney Docket No: 303.689US2	

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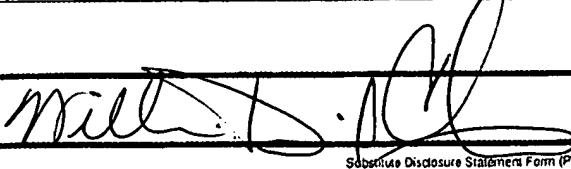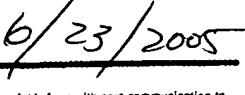| Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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	Examiner Name	~~Unknown~~ W. DAVID COLEMAN
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